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ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is characterized in that an angle θ of inclination formed by the side surfaces of a ridge portion and a lower part of the ridge portion is at least 70° and not more than 117° , a p-type cladding layer is made of $\text{Al}_{x_1}\text{Ga}_{1-x_1}\text{As}$, a first current blocking layer is made of $\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$, the distance between an emission layer and the first current blocking layer satisfies the relation of $t \leq 0.275/(1 - (x_2 - x_1))$ assuming that t represents the distance, and a lower width W of the ridge portion is at least $2 \mu\text{m}$ and not more than $5 \mu\text{m}$.

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